

#### Features

High collector to emitter voltage: VcEo>120V.



## Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	120	V
Collector-emitter voltage	Vceo	120	V
Emitter-base voltage	VEBO	5	V
Collector current	lc	0.7	Α
Collector current (pulse) *	IC (pu)	1.2	А
Collector power dissipation	Pc	2	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

<sup>\*.</sup> PW≤10ms,duty cycle≤50%

### Electrical Characteristics Ta = 25<sup>o</sup>C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Base-emitter voltage *	VBE	VcE =10V , Ic = 10mA	550	620	650	mV
Collector cutoff current	Ісво	VcB = 120V, IE=0			100	nA
Emitter cutoff current	lebo	VEB = 5V, IC=0			100	nA
DC current gain *	hFE	VcE =1V , Ic = 5.0mA	45	200		
		VcE =1V , Ic = 100mA	90	200	400	
Collector-emitter saturation voltage *	VCE(sat)	Ic = 500mA , IB = 50mA		0.3	0.6	٧
Base-emitter saturation voltage *	VBE(sat)	Ic = 500mA , Iв = 50mA		0.9	1.5	V
Output capacitance	Cob	VcB = 10V , IE = 0 , f = 1.0MHz		10		pF
Transition frequency	fт	VcE = 10V , IE = -10mA		90		MHz

<sup>\*.</sup> PW≤350µs,duty cycle≤2%

### hFE Classification

Marking	HR	HQ	HP
hFE	90~180	135~270	200~400

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